NPN General - Purpose Amplifier

2N3904

Description

This device is designed as a general-purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier.

MAXIMUM RATINGS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.) (Note 1, Note 2)

Symbol	Parameter	Value	Unit
V _{CEO}	Collector – Emitter Voltage	40	V
V _{CBO}	Collector – Base Voltage	60	V
V _{EBO}	Emitter – Base Voltage	6.0	V
Ι _C	Collector Current – Continuous	200	mA
T _J , T _{STG}	T _J , T _{STG} Operating and Storage Junction –55 to - Temperature Range		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 These ratings are based on a maximum junction temperature of 150°C.
These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed orlow-duty cycle operations.

THERMAL CHARACTERISTICS

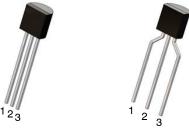
(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Max	Unit
P _D	Total Device Dissipation	625	mW
	Derate Above 25°C	5.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	°C/W



ON Semiconductor®

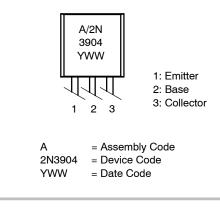
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TO-92 3 CASE 135AN

TO-92 3 LEADFORMED CASE 135AR

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

ELECTRICAL CHARACTERISTICS (Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parametr	Conditions	Min	Max	Unit
OFF CHARACTEF	RISTICS		•		
V _{(BR)CEO}	Collector - Emitter Breakdown Voltage	I _C = 1.0 mA, I _B = 0	40	-	V
V _{(BR)CBO}	Collector - Base Breakdown Voltage	$I_{C} = 10 \ \mu A, \ I_{E} = 0$	60	-	V
V _{(BR)EBO}	Emitter – Base Breakdown Voltage	$I_{E} = 10 \ \mu A, \ I_{C} = 0$	6.0	-	V
I _{BL}	Base Cutoff Current	V_{CE} = 30 V, V_{EB} = 3 V	-	50	nA
I _{CEX}	Collector Cut-Off Current	V_{CE} = 30 V, V_{EB} = 3 V	-	50	nA
ON CHARACTERI	STICS (Note 3)				
h _{FE}	DC Current Gain	I_{C} = 0.1 mA, V_{CE} = 1.0 V	40	-	-
		I_{C} = 1.0 mA, V_{CE} = 1.0 V	70	-	1
		I_{C} = 10 mA, V_{CE} = 1.0 V	100	300	1
		I_{C} = 50 mA, V_{CE} = 1.0 V	60	-	1
		I _C = 100 mA, V _{CE} = 1.0 V	30	-	1
V _{CE(sat)}	Collector - Emitter Saturation Voltage	I _C = 10 mA, I _B = 1.0 mA	-	0.2	V
		I _C = 50.0 mA, I _B = 5.0 mA	-	0.3	1
V _{BE(sat)}	Base - Emitter Saturation Voltage	I _C = 10.0 mA, I _B = 1.0 mA	0.65	0.85	V
		I _C = 50.0 mA, I _B = 5.0 mA	_	0.95	1

SMALL-SIGNAL CHARACTERISTICS

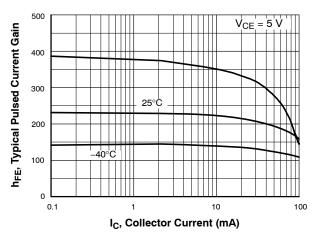
fT	Current-Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V}, f = 100 \text{ MHz}$	300	-	MHz
C _{obo}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, \text{ I}_{E} = 0,$ f = 100 kHz	-	4.0	pF
C _{ibo}	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_{C} = 0, f = 100 \text{ kHz}$	-	8.0	pF
NF	Noise Figure	$ \begin{array}{l} I_{C} = 100 \; \mu A, \; V_{CE} = 5.0 \; V, \\ R_{S} = 1.0 \; k \Omega, \\ f = 10 \; Hz \; to \; 15.7 \; kHz \end{array} $	-	5.0	dB

SWITCHING CHARACTERISTICS

t _d	Delay Time	$V_{CC} = 3.0 \text{ V}, V_{BE} = 0.5 \text{ V},$ $I_{C} = 10 \text{ mA}, I_{B1} = 1.0 \text{ mA}$	_	35	ns
t _r	Rise Time	$IC = 10 IIIA, IB_1 = 1.0 IIIA$	-	35	ns
t _s	Storage Time	$V_{CC} = 3.0 \text{ V}, I_{C} = 10 \text{ mA},$	-	200	ns
t _f	Fall Time	$I_{B1} = I_{B2} = 1.0 \text{ mA}$	-	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width ≤ 300 µs; Duty Cycle ≤ 2%.

TYPICAL PERFORMANCE CHARACTERISTICS





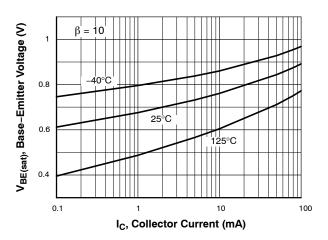


Figure 3. Base–Emitter Saturation Voltage vs. Collector Current

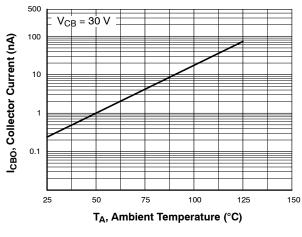


Figure 5. Collector Cut–Off Current vs. Ambient Temperature

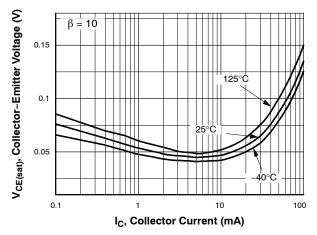


Figure 2. Collector–Emitter Saturation Voltage vs. Collector Current

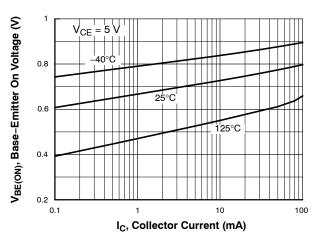


Figure 4. Base–Emitter On Voltage vs. Collector Current

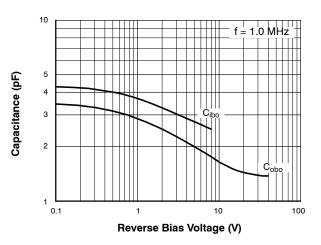


Figure 6. Capacitance vs. Reverse Bias Voltage



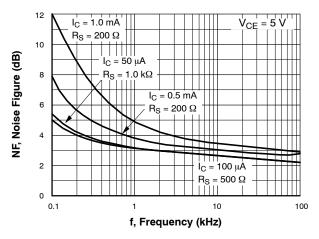


Figure 7. Noise Figure vs. Frequency

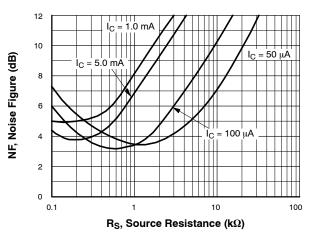


Figure 8. Noise Figure vs. Source Resistance

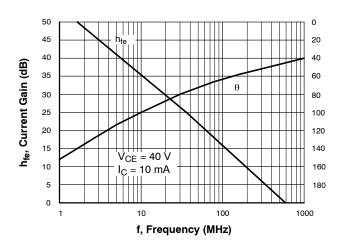


Figure 9. Current Gain and Phase Angle vs. Frequency

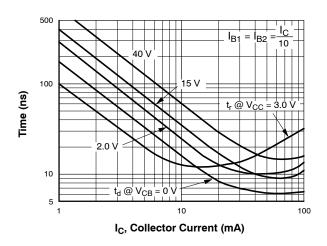


Figure 11. Turn-On Time vs. Collector Current

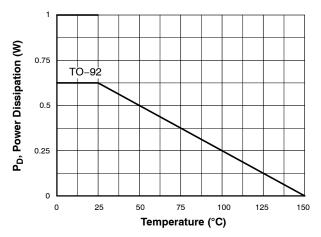


Figure 10. Power Dissipation vs. Ambient Temperature

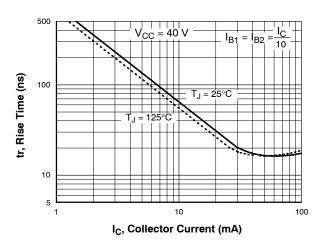


Figure 12. Rise Time vs. Collector Current

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

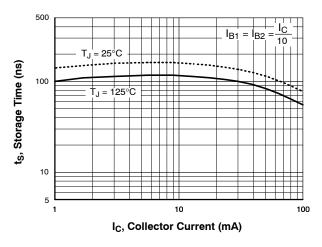


Figure 13. Storage Time vs. Collector Current

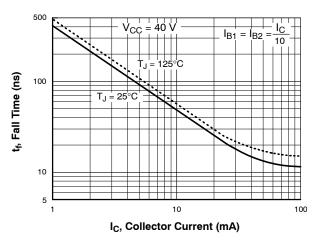
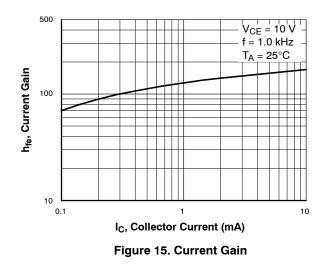
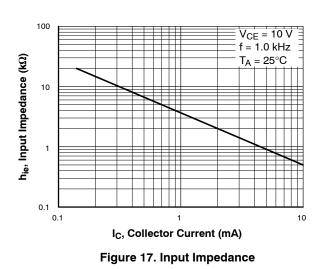


Figure 14. Fall Time vs. Collector Current





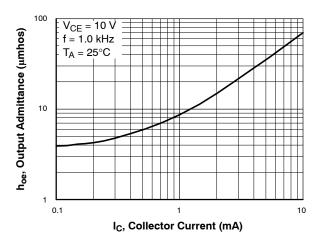


Figure 16. Output Admittance

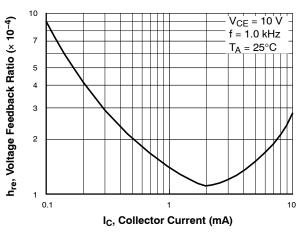
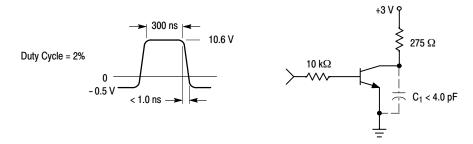
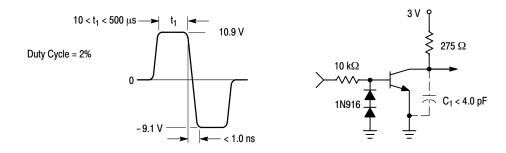


Figure 18. Voltage Feedback Ratio

TEST CIRCUITS







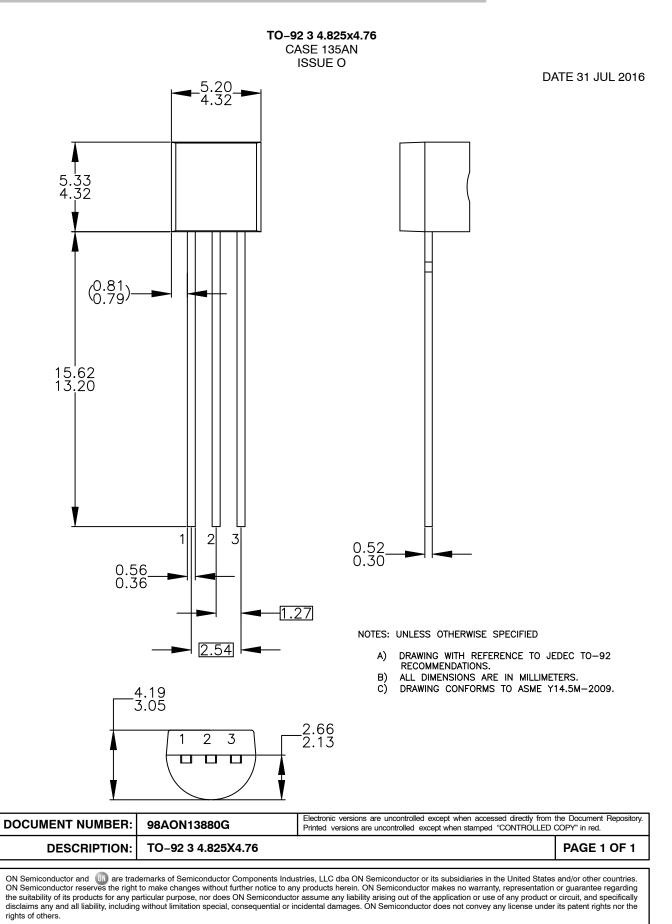


ORDERING INFORMATION

Device	Package	Shipping [†]
2N3904BU	TO–92–3 LF (Pb–Free)	10000 Units / Bulk Bag
2N3904TA	TO–92–3 LF (Pb–Free)	2000 Units / Fan-Fold
2N3904TAR	TO-92-3 LF (Pb-Free)	2000 Units / Fan-Fold
2N3904TF	TO-92-3 LF (Pb-Free)	2000 Units / Tape & Reel
2N3904TFR	TO–92–3 LF (Pb–Free)	2000 Units / Tape & Reel

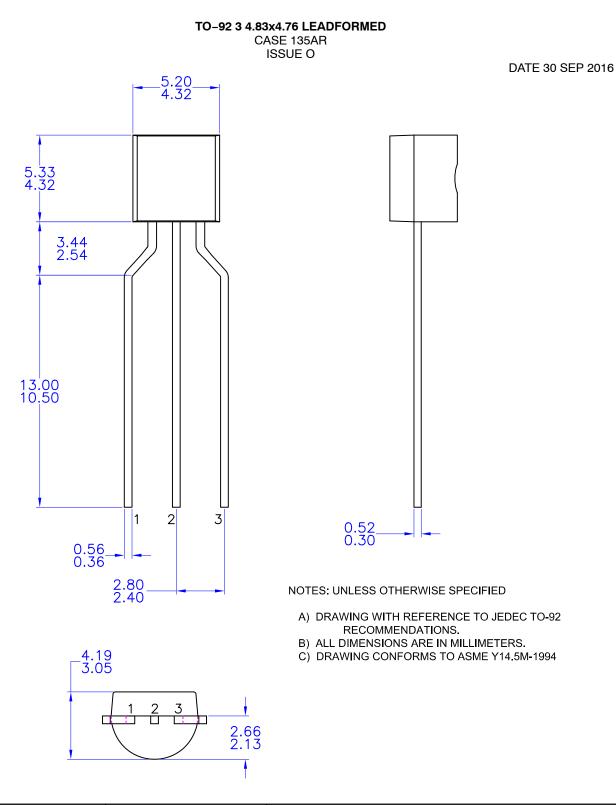
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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